CMPT491E

SURFACE MOUNT NPN SILICON TRANSISTOR



SOT-23 CASE

MAXIMUM RATINGS: $(T_A=25^{\circ}C)$

Operating and Storage

Junction Temperature

Thermal Resistance

Central ** Semiconductor Corp.

-65 to +150

357

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT491E type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current, general purpose amplifier applications. **Marking Code is C49.**

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	IC	1.0	Α
Base Current	ΙΒ	200	mA
Collector Current (Peak)	I _{CM}	2.0	Α
Power Dissipation	PD	350	mW

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

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SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =60V		100	nA
I _{EBO}	V _{EB} =4.0V		100	nA
BV _{CBO}	I _C =100μA	80		V
BVCEO	I _C =10mA	60		V
BVEBO	I _E =100μA	5.0		V
V _{CE(SAT)}	I _C =500mA, I _B =50mA		0.20	V
V _{CE(SAT)}	I _C =1.0A, I _B =100mA		0.40	V
V _{BE} (SAT)	I _C =1.0A, I _B =100mA		1.1	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =1.0A		1.0	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	200		
h _{FE}	V _{CE} =5.0V, I _C =500mA	200	600	
h _{FE}	V _{CE} =5.0V, I _C =1.0A	50		
h _{FE}	V_{CE} =5.0V, I_{C} =2.0A	15		
f _T	V _{CE} =10V, I _C =50mA, f=100MHz	150		MHz
Coh	V_{CB} =10V, I_{E} =0, f=1.0MHz		10	pF

R2 (31-August 2001)

°C

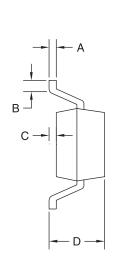
°C/W

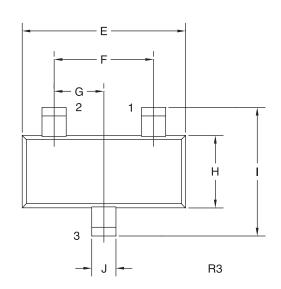


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SURFACE MOUNT NPN SILICON TRANSISTOR

SOT-23 CASE - MECHANICAL OUTLINE





LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C49

DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	0.003	0.007	0.08	0.18			
В	0.006	-	0.15	-			
С	-	0.005	-	0.13			
D	0.035	0.043	0.89	1.09			
E	0.110	0.120	2.80	3.05			
F	0.075		1.90				
G	0.037		0.95				
Н	0.047	0.055	1.19	1.40			
	0.083	0.098	2.10	2.49			
J	0.014	0.020	0.35	0.50			

SOT-23 (REV: R3)